TAYCHIPST

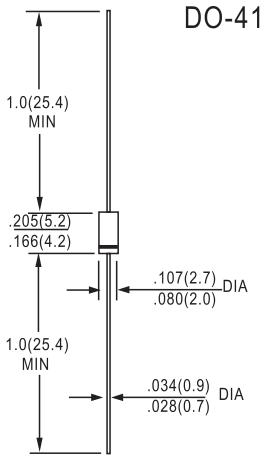
PLASTIC SILICON RECTIFIER

ERB12-01 THRU ERB12-10

50V-1000V 1.0A

FEATURES

- Low cost
- Diffused junction
- Low leakage
- Low forward voltage drop
- High current capability
- Easily cleaned with Freon,Alcohol,Isopropanol
- and similar solvents
- The plastic material carries U/L recognition 94V-0



Dimensions in inches and (millimeters)

MECHANICAL DATA

Case:JEDEC DO--41,molded plastic
Terminals: Axial lead ,solderable per
MIL- STD-202,Method 208
Polarity: Color band denotes cathode
Weight: 0.012ounces,0.34 grams
Mounting position: Any

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.
Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

		ERB12 -01	ERB12 -02	ERA12 -04	ERB12 -06	ERB12 -10	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	100	200	400	600	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	700	V
Maximum DC blocking voltage	V_{DC}	100	200	400	600	1000	V
Maximum average forw ard rectified current 9.5mm lead length, @T_A=75℃	$I_{F(AV)}$	1.0					A
Peak forw ard surge current 8.3ms single half-sine-w ave superimposed on rated load @T_J=125℃	I_{FSM}	60.0					A
Maximum instantaneous forw ard voltage @ 1.0 A	V_F	1.1					V
Maximum reverse current @T_A=25℃ at rated DC blocking voltage @T_A=100℃	I_R	5.0 50.0					μA
Typical junction capacitance (Note1)	C_J	15					pF
Typical thermal resistance (Note2)	$R_{\theta JA}$	50					℃/W
Operating junction temperature range	T_J	- 55---- + 150					℃
Storage temperature range	T_{STG}	- 55 ---- +150					℃

NOTE: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
2. Thermal resistance from junction to ambient.

RATINGS AND CHARACTERISTIC CURVES ERB12-01 THRU ERB12-10

FIG.1 -- TYPICAL FORWARD CHARACTERISTIC

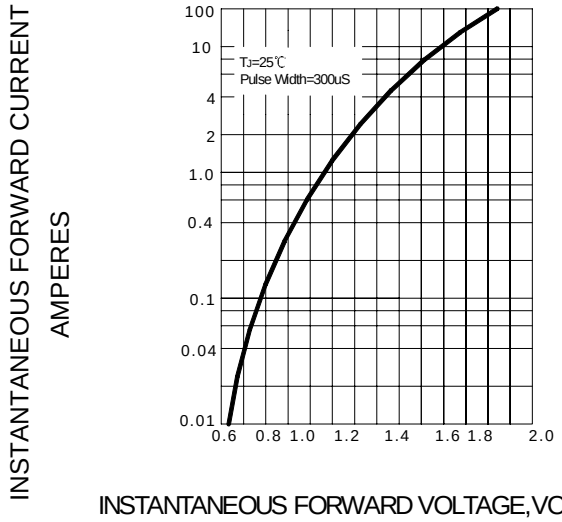


FIG.2 -- TYPICAL JUNCTION CAPACITANCE

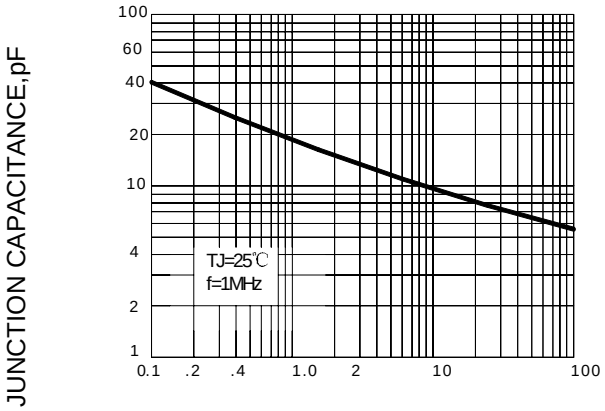


FIG.3 -- PEAK FORWARD SURGE CURRENT

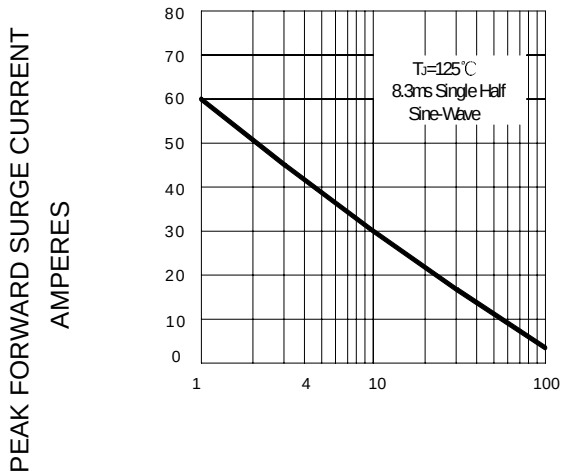


FIG.4 -- FORWARD DERATING CURVE